

# **MOSFET** - Power, N-Channel, SOT-23 200 mA, 50 V

# BSS138L, BVSS138L

Typical applications are DC-DC converters, power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

#### **Features**

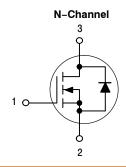
- Low Threshold Voltage (V<sub>GS(th)</sub>: 0.85 V-1.5 V) Makes it Ideal for Low Voltage Applications
- Miniature SOT-23 Surface Mount Package Saves Board Space
- HBM Class 0A, MM Class M1A, CDM Class IV (Note 3)
- BVSS Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

## MAXIMUM RATINGS (T<sub>A</sub> = 25°C unless otherwise noted)

| Rating   | Symbol                            | Value       | Unit |
|--|-----------------------------------|-------------|------|
| Drain-to-Source Voltage  | V <sub>DSS</sub>                  | 50          | Vdc  |
| Gate-to-Source Voltage - Continuous  | V <sub>GS</sub>                   | ± 20        | Vdc  |
| Drain Current - Continuous @ $T_A = 25^{\circ}C$ - Pulsed Drain Current $(t_p \le 10 \ \mu s)$ | I <sub>D</sub><br>I <sub>DM</sub> | 200<br>800  | mA   |
| Total Power Dissipation @ T <sub>A</sub> = 25°C  | $P_{D}$                           | 225         | mW   |
| Operating and Storage Temperature Range  | T <sub>J</sub> , T <sub>stg</sub> | – 55 to 150 | °C   |
| Thermal Resistance, Junction-to-Ambient  | $R_{	heta JA}$                    | 556         | °C/W |
| Maximum Lead Temperature for Soldering Purposes, for 10 seconds                                | TL                                | 260         | °C   |
|  |                                   |             |      |

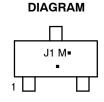
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

200 mA, 50 V  $R_{DS(on)} = 3.5 \Omega$ 





SOT-23 **CASE 318** STYLE 21



MARKING

J1 = Device Code М = Date Code\* = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

#### ORDERING INFORMATION

| Device                     | Package             | Shipping <sup>†</sup> |
|----------------------------|---------------------|-----------------------|
| BSS138LT1G,<br>BVSS138LT1G | SOT-23<br>(Pb-Free) | 3,000 / Tape & Reel   |
| BSS138LT7G                 | SOT-23<br>(Pb-Free) | 3,500 / Tape & Reel   |
| BSS138LT3G,<br>BVSS138LT3G | SOT-23<br>(Pb-Free) | 10,000 / Tape & Reel  |

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

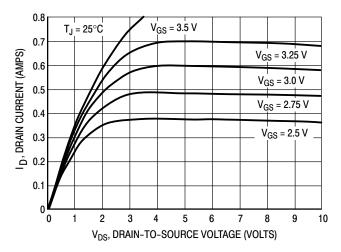
|  | Symbol   | Min                 | Тур         | Max         | Unit              |      |
|--|--|---------------------|-------------|-------------|-------------------|------|
| OFF CHARACTERISTICS  |  |                     |             |             | •                 |      |
| Drain-to-Source Breakdown Vo<br>(V <sub>GS</sub> = 0 Vdc, I <sub>D</sub> = 250 μAdc)   | V <sub>(BR)DSS</sub>                                       | 50                  | -           | -           | Vdc               |      |
| Zero Gate Voltage Drain Current $ (V_{DS} = 25 \text{ Vdc}, V_{GS} = 0 \text{ Vdc}, 25^{\circ}\text{C}) $ $ (V_{DS} = 50 \text{ Vdc}, V_{GS} = 0 \text{ Vdc}, 25^{\circ}\text{C}) $ $ (V_{DS} = 50 \text{ Vdc}, V_{GS} = 0 \text{ Vdc}, 150^{\circ}\text{C}) $ |  | I <sub>DSS</sub>    | -<br>-<br>- | -<br>-<br>- | 0.1<br>0.5<br>5.0 | μAdc |
| Gate-Source Leakage Current (V <sub>GS</sub> = ± 20 Vdc, V <sub>DS</sub> = 0 Vdc)  |  | I <sub>GSS</sub>    | _           | -           | ±0.1              | μAdc |
| ON CHARACTERISTICS (Note 1   |  |                     |             |             |                   |      |
| Gate-Source Threshold Voltage $(V_{DS} = V_{GS}, I_D = 1.0 \text{ mAdc})$  | V <sub>GS(th)</sub>  | 0.85                | -           | 1.5         | Vdc               |      |
| Static Drain–to–Source On–Resistance $(V_{GS}=2.75~Vdc,~I_D<200~mAdc,~T_A=-40^{\circ}C~to~+85^{\circ}C) \\ (V_{GS}=5.0~Vdc,~I_D=200~mAdc)$   |  | r <sub>DS(on)</sub> | _<br>_      | 5.6<br>-    | 10<br>3.5         | Ω    |
| Forward Transconductance<br>(V <sub>DS</sub> = 25 Vdc, I <sub>D</sub> = 200 mAdd   | 9 <sub>fs</sub>  | 100                 | -           | -           | mmhos             |      |
| DYNAMIC CHARACTERISTICS  |  |                     |             |             |                   |      |
| Input Capacitance  | (V <sub>DS</sub> = 25 Vdc, V <sub>GS</sub> = 0, f = 1 MHz) | C <sub>iss</sub>    | _           | 40          | 50                | pF   |
| Output Capacitance   | (V <sub>DS</sub> = 25 Vdc, V <sub>GS</sub> = 0, f = 1 MHz) | C <sub>oss</sub>    | _           | 12          | 25                | 1    |
| Transfer Capacitance   | (V <sub>DG</sub> = 25 Vdc, V <sub>GS</sub> = 0, f = 1 MHz) | C <sub>rss</sub>    | _           | 3.5         | 5.0               | 1    |
| SWITCHING CHARACTERISTIC   | S (Note 2)   | •                   | •           | -           | •                 | •    |
| Turn-On Delay Time   | () (0)/4-1 (0,0)4-)  | t <sub>d(on)</sub>  | _           | -           | 20                | ns   |
| Turn-Off Delay Time  | (V <sub>DD</sub> = 30 Vdc, I <sub>D</sub> = 0.2 Adc,)      | t <sub>d(off)</sub> | _           | _           | 20                |      |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
 Switching characteristics are independent of operating junction temperature.

<sup>3.</sup> ESD between the gate and source serves only, no gate overvoltage rating is implied.

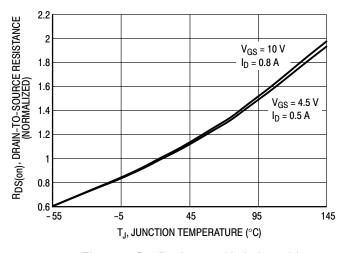
### TYPICAL ELECTRICAL CHARACTERISTICS



0.9 25°C  $V_{DS} = 10 V$ 0.8 -55°C ID, DRAIN CURRENT (AMPS) 0.7 150°C 0.6 0.5 0.4 0.3 0.2 0.1 0.5 3 3.5 4.5 VGS, GATE-TO-SOURCE VOLTAGE (VOLTS)

Figure 1. On-Region Characteristics

Figure 2. Transfer Characteristics



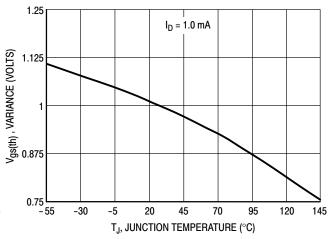
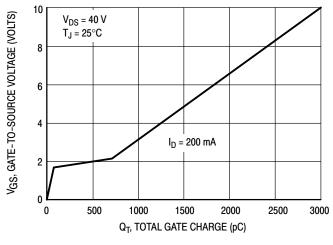


Figure 3. On–Resistance Variation with Temperature

Figure 4. Threshold Voltage Variation with Temperature



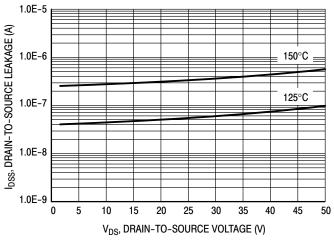
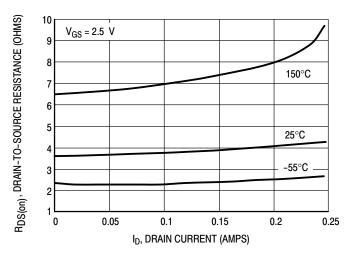


Figure 5. Gate Charge

Figure 6. IDSS

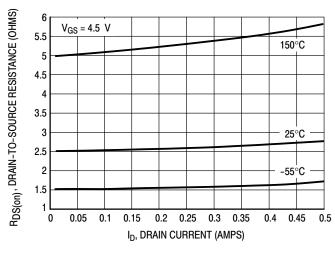
### TYPICAL ELECTRICAL CHARACTERISTICS



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Figure 7. On-Resistance versus Drain Current

Figure 8. On-Resistance versus Drain Current



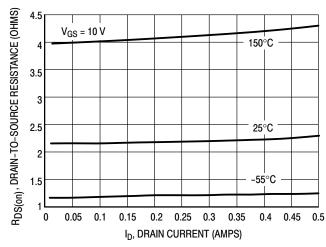
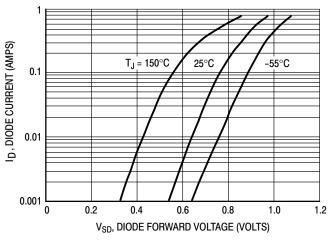


Figure 9. On-Resistance versus Drain Current

Figure 10. On-Resistance versus Drain Current



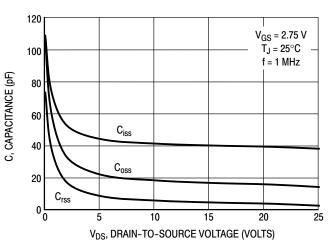


Figure 11. Body Diode Forward Voltage

Figure 12. Capacitance

# TYPICAL ELECTRICAL CHARACTERISTICS

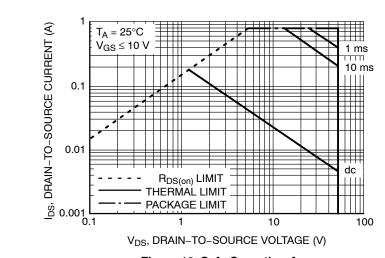


Figure 13. Safe Operating Area

**MILLIMETERS** 

MIN

0.89

0.01

0.37

0.08

2.80

1.20

1.78

0.30

0.35

2.10

O°

NOM

1.00

0.06

0.44

0.14

2.90

1.30

1.90

0.43

0.54

2.40

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### SOT-23 (TO-236) 2.90x1.30x1.00 1.90P **CASE 318 ISSUE AU**

**DATE 14 AUG 2024** 

MAX

1.11

0.10

0.50

0.20

3.04

1.40

2.04

0.55

0.69

2.64

10°





DETAIL "A" Scale 3:1







#### NOTES:

DIM

Α

Α1

b

С

D

Ε

е L

L1

HE

Τ

- DIMENSIONING AND TOLERANCING 1. PER ASME Y14.5M, 2018. CONTROLLING DIMENSIONS:
- MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE
- BASE MATERIAL.
  DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

## **GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code

= Date Code

= Pb-Free Package

## RECOMMENDED MOUNTING FOOTPRINT

\* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

### **STYLES ON PAGE 2**

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<sup>\*</sup>This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.

# SOT-23 (TO-236) 2.90x1.30x1.00 1.90P CASE 318 ISSUE AU

DATE 14 AUG 2024

| STYLE 1 THRU 5:<br>CANCELLED                            | STYLE 6:<br>PIN 1. BASE<br>2. EMITTER<br>3. COLLECTOR |               |   |   |
|---|---|---------------|---|---|
| STYLE 9:<br>PIN 1. ANODE<br>2. ANODE<br>3. CATHODE      | STYLE 10:<br>PIN 1. DRAIN<br>2. SOURCE<br>3. GATE     | 2. CATHODE 2. | 2: STYLE 13: CATHODE PIN 1. SOURCE CATHODE 2. DRAIN ANODE 3. GATE                 | STYLE 14:<br>PIN 1. CATHODE<br>2. GATE<br>3. ANODE          |
| STYLE 15:<br>PIN 1. GATE<br>2. CATHODE<br>3. ANODE      | STYLE 16:<br>PIN 1. ANODE<br>2. CATHODE<br>3. CATHODE | 2. ANODE 2.   | 3: STYLE 19: NO CONNECTION PIN 1. CATHODE CATHODE 2. ANODE ANODE 3. CATHODE-ANODE | STYLE 20:<br>PIN 1. CATHODE<br>2. ANODE<br>3. GATE          |
| STYLE 21:<br>PIN 1. GATE<br>2. SOURCE<br>3. DRAIN       | STYLE 22:<br>PIN 1. RETURN<br>2. OUTPUT<br>3. INPUT   |               |   | STYLE 26:<br>PIN 1. CATHODE<br>2. ANODE<br>3. NO CONNECTION |
| STYLE 27:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. CATHODE | STYLE 28:<br>PIN 1. ANODE<br>2. ANODE<br>3. ANODE     |               |   |   |

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